

PATENT ABSTRACTS OF JAPAN

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FUJITSU VLSI LTD

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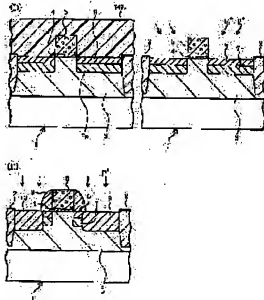
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OKABE KENICHI
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(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device capable of forming a pocket area by using indium and decreasing the increase of leak current by ion injection of indium.

SOLUTION: The semiconductor device has first and second active areas demarcated on the main surface of a silicon substrate, a first n channel MOS transistor formed on the first active area having a first extension area and a first pocket area adding the indium of first concentration at a position deeper than the first extension area, and a second n channel MOS transistor formed on the second active area having a second extension area and a second pocket area adding the indium of second concentration lower than the first concentration at another position deeper than the second extension area. Furthermore, boron may be ion-injected in the second pocket area.



LEGAL STATUS

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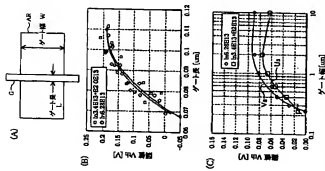
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【特許補正2】

【図出日】平成13年12月19日(2001.12.19)

【図4】

【特許補正1】

【特許対象発明名】図5

【特許対象項目名】図4

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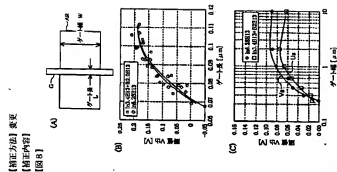
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【特許補正1】

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